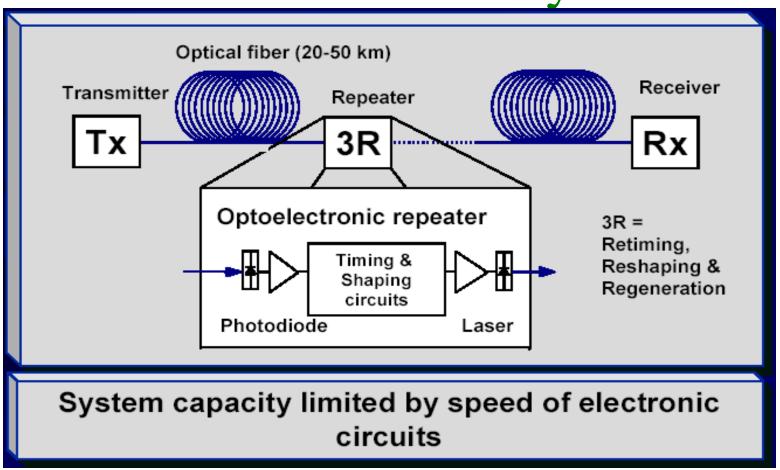
Optical Amplifiers An Important Element of WDM Systems

Optical Amplifiers

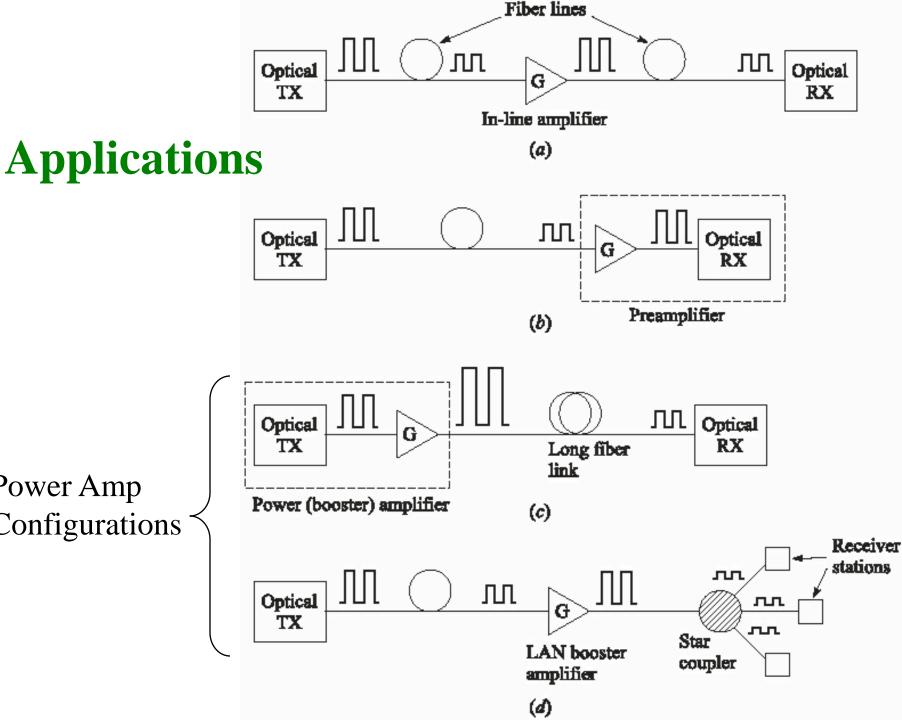
- Conventional Repeaters in N-WDM systems are very inefficient:
 - Wavelength de-multiplexing →
 - O/E conversion → electrical amplification
 → retiming → pulse shaping → E/O
 times conversion}
 - wavelength multiplexing
- Optical Amplifiers: A single device that amplify multiple format signals that are carried by multiple wavelengths

Traditional Optical Communication System



Optical Amplification

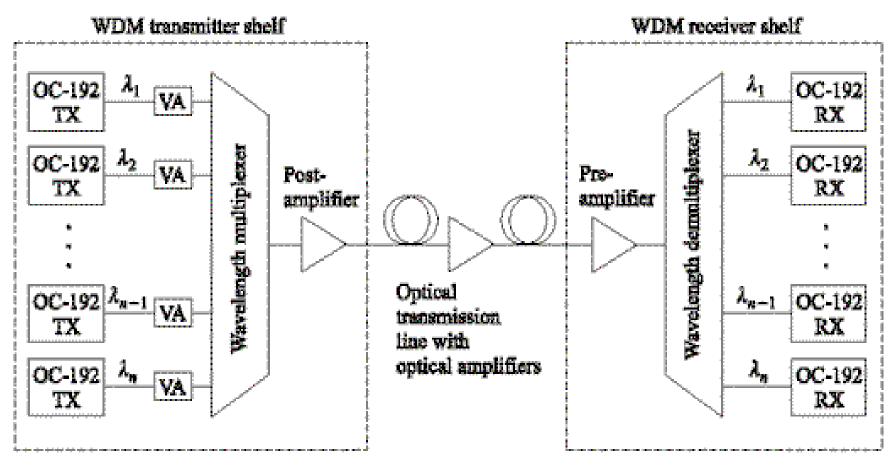
- Variety of optical amplifier types exist, including:
 - Semiconductor optical amplifiers
 - Optical fibre amplifiers (Erbium Doped Fibre Amplifiers)
 - Distributed fibre amplifiers (Raman Amplifiers)
- Optical fibre amplifiers are now the most common type
- One of the most successful optical processing functions
- Also used as a building block in DWDM systems



Power Amp

Configurations

Nortel OPTERA System



TX: Optical transmitter

RX: Optical receiver

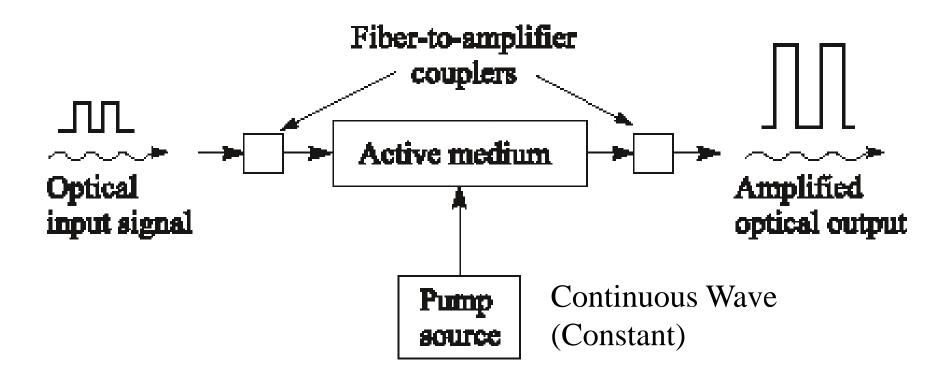
VA: Variable attenuator

64 wavelengths each carrying 10 Gb/s

Basic Concepts

- Most optical amplifiers use stimulated emission
- An optical amplifier is basically a laser without feedback
- Optical gain is realized when the amplifier is pumped optically (or electrically) to achieve *population* inversion
- Gain depends on wavelength, internal light intensity and amplifier medium
- Two types: semiconductor optical amplifiers and fiber doped amplifiers

Generic optical amplifier



Energy is transferred from the pump to signal

Semiconductor Optical Amplifiers

- Similar to Laser diodes but the emission is triggered by input optical signal
- Work in any wavelength (+)
- Have high integration, compact and low power consumption (+)
- Gain fluctuation with signal bit rate (-)
- Cross talk between different wavelengths (-)
- External Current injection pumping method
- Two types: Fabry-Perot or <u>Traveling Wave Amp.</u>

External Pumping

Current injection -> ext. pur Clip slide amplify optical signals via stimulated emission=> PI

Rate equation

carrier density in excited state stimulated emission

$$\frac{\partial n(t)}{\partial t} = R_p(t) - R_{st}(t) - \frac{n(t)}{\tau_r}$$
external pumping rate

combined time constant coming from spontaneouscarrier recombination mechanism

current density

$$R_p(t) = \frac{J(t)}{qd}$$
 thickness of active area

charge carrier

threshold carrier density photon density power of optical signal group velocity

$$R_{st}(t) = \Gamma a v_g (n - n_{th}) N_{ph} \equiv g v_g N_{ph}$$

gain constant overall gain per unit of length

optical confinement factor

$$N_{ph} = \frac{P_z}{v_g(hv)(wd)}$$
width of active

energy of photon

area

Under steady state condition, variation of n vs time is zero, therefore:

$$R_p = R_{st} + \frac{n}{\tau_r}$$

$$R_p(t) = \frac{J(t)}{qd}$$

$$R_{st}(t) = \Gamma a v_g (n - n_{th}) N_{ph} \equiv g v_g N_{ph}$$

$$g = \frac{\frac{J}{qd} - \frac{n_{th}}{\tau_r}}{v_g N_{ph} + 1/(\Gamma a \tau_r)} = \frac{\frac{Gain \text{ is increased with increasing current injection}}{1 + N_{ph}/N_{ph;sat}}$$

$$N_{ph;sat} = \frac{1}{\Gamma a v_g \tau_r}$$

Gain is saturated with increasing photon density
Saturation photon density

$$g_0 = \Gamma a \tau_r \left(\frac{J}{qd} - \frac{n_{th}}{\tau_r} \right)$$

g_o is the zero or small-signal gain per unit of length (in the absence of the signal input)

Amplifier Gain

Amplifier gain , $G = \frac{p_{z,out}}{2}$

 $P_{e,in}$ = Input power of optical signal

 $P_{x,out}$ = Output power of amplified optical signal

Same as that of LASER.

$$G = e^{(\Gamma g_m - \widetilde{\alpha})L} = e^{(g(z))L}$$

Where.

- G = single pass gain in active medium of SOA
- gm = The material gain coefficient
- α = Effective absorption coefficient of the material
- L = Amplifier length respectively

g(z) = overall gain per unit of length (depends on the carrier density & s/l wavelength)

From the eqn,

G, gain \(\gamma\) with device length & the internal gain is limited by gain saturation.

i/p power $\uparrow => G \uparrow => EHP$ depleted from the active region => will not have enough EHP in the active region to be stimulated=> gain saturation

large optical input => Gain saturates

g(z) can written as $\frac{g_0}{1 + \frac{P_S(Z)}{P_{amp,sat}}}$

 g_0 = unsaturated medium gain per unit of length in the absence of signal input

 $P_S(z)$ = internal signal power at point z.

 $P_{amp,sat}$ = amplifier saturation power

The increase in the light power in incremental length of dz can be expressed as:

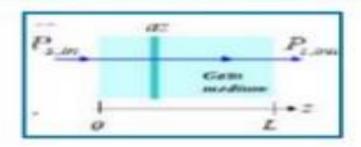
$$dP = g(z) P_S(Z) dz = \frac{g_0}{1 + \frac{P_S(Z)}{P_{amp,sat}}} P_S(z) dz$$

Solving for g_0 ,

$$g_0 dz = dP \left\{ 1 + \frac{P_S(Z)}{P_{amp,sat}} \right\} \frac{1}{P_S(Z)} dz$$

$$g_0 \mathrm{dz} = \mathrm{dP} \left\{ \frac{1}{P_S(Z)} + \frac{P_S(Z)}{P_S(Z) \; P_{amp,sat}} \right\} \mathrm{dz}$$

$$g_0 dz = dP \left\{ \frac{1}{P_S(z)} + \frac{1}{P_{amp,sat}} \right\} dz$$



Now integrating both sides with

$$\int_0^L g_0 dz = \int_{P_{s,in}}^{P_{s,out}} \left\{ \frac{1}{P_s(z)} + \frac{1}{P_{amp,sat}} \right\} dz$$

$$\begin{split} \int_{0}^{L} g_{0} dz &= g_{0} \int_{0}^{L} dz = g_{0}[z]_{0}^{L} = g_{0}[L - 0] = g_{0}L \dots \dots 0 \\ \int_{P_{z,in}}^{P_{z,out}} \left\{ \frac{1}{P_{S}(Z)} + \frac{1}{P_{amp,sat}} \right\} dz \\ &= > \int_{P_{z,in}}^{P_{z,out}} \left\{ \frac{1}{P_{S}(Z)} \right\} dz + \int_{P_{z,in}}^{P_{z,out}} \left\{ \frac{1}{P_{amp,sat}} \right\} dz \\ &= \left[\ln P_{S}(Z) \right]_{P_{s,in}}^{P_{z,out}} + \frac{1}{P_{amp,sat}} \left[z \right]_{P_{z,in}}^{P_{z,out}} \\ &= \ln (P_{z,out}) - \ln (P_{s,in}) + \left\{ \frac{P_{z,out} - P_{z,in}}{P_{amp,sat}} \right\} \end{split}$$

$$\ln(\frac{P_{s,out}}{P_{s,in}}) + \{\frac{P_{s,out} - P_{s,in}}{P_{amp,sat}}\} = g_0 L$$

single pass gain in absence of light = $e^{(g_0 L)}$

$$\ln(G) + P_{s,in} \left\{ \frac{\frac{P_{s,out}}{P_{s,in}} 1}{P_{amp,sat}} \right\} = \ln(G_0)$$

$$\Leftrightarrow \left\{ \frac{G-1}{\frac{P_{amp,sat}}{P_{s,in}}} \right\} = \ln(G_0) - \ln(G)$$

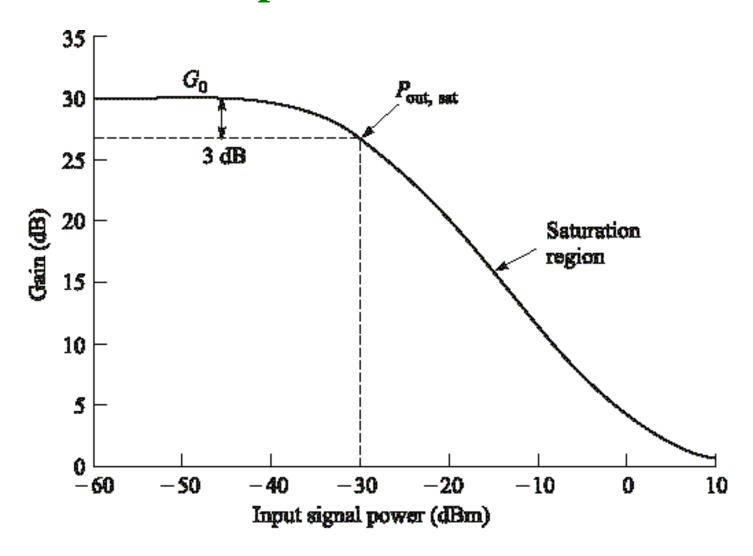
$$\Rightarrow \left\{ \frac{G-1}{\frac{P_{amp,sat}}{P_{x,tn}}} \right\} = \ln(\frac{G_0}{G})$$

Solving for G,

$$\Rightarrow G - 1 = \ln(\frac{G_0}{G}) \left\{ \frac{P_{amp,sat}}{P_{s,in}} \right\}$$

$$\Rightarrow G = 1 + \ln(\frac{G_0}{G}) \left\{ \frac{P_{amp.sat}}{P_{s.in}} \right\}$$

Solid State Amplifier Gain versus Power

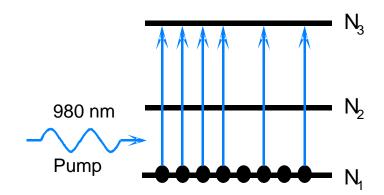


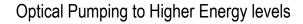
Distributed Fiber Amplifiers

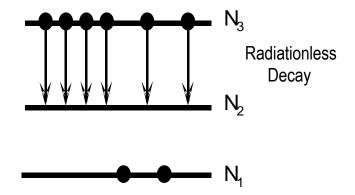
- The active medium is created by lightly doping silica fiber core by rare earth element Ex: Erbium (Er)
- Long fiber length (10-30 m)
- Low coupling loss (+)
- Transparent to signal format and bit rate
- No cross talk
- Broad output spectrum (1530 1560 nm)

Works only in specific Wavelengths

Amplification Process of EDFA







Rapid Relaxation to "metastable" State

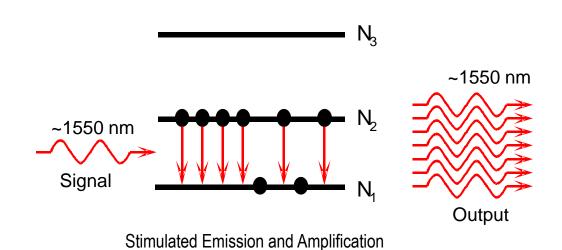
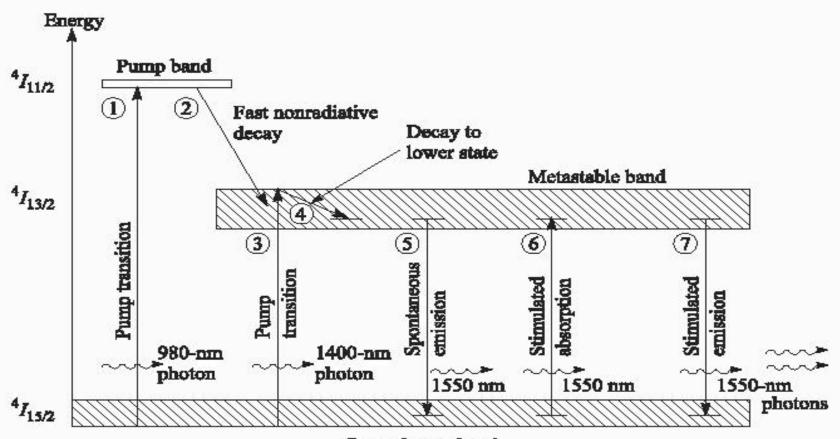
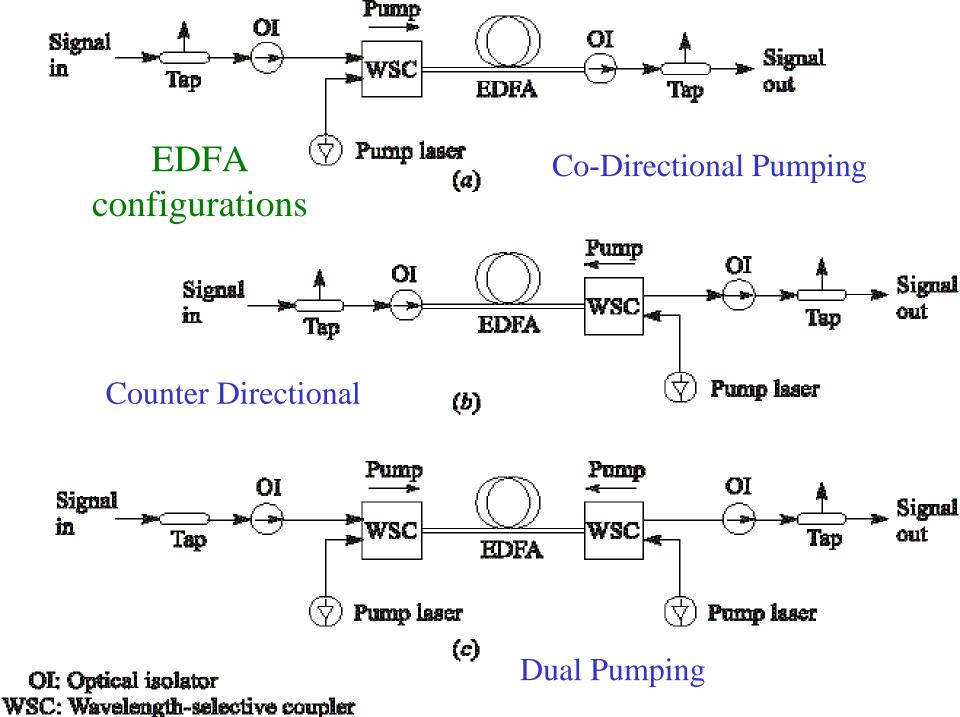


Fig. 11-4: Erbium energy-level diagram



Ground-state band



EDFA Power-Conversion Efficiency and Gain

The input and output signal powers of an EDFA

$$P_{s,\text{out}} \leq P_{s,\text{in}} + \frac{\lambda_p}{\lambda_s} P_{p,\text{in}}$$

maximum output signal power depends on the ratio $\lambda p/\lambda s$. For the pumping scheme to work, we need to have $\lambda p < \lambda s$, and, to have an appropriate gain, it is necessary that Ps,in \leq Pp,in. Thus, the power conversion efficiency (PCE), defined as

PCE =
$$\frac{P_{s,\text{out}} - P_{s,\text{in}}}{P_{p,\text{in}}} \approx \frac{P_{s,\text{out}}}{P_{p,\text{in}}} \le \frac{\lambda_p}{\lambda_s} \le 1$$

$$QCE = \frac{\lambda_s}{\lambda_p} PCE$$

EDFA

$$G = \frac{P_{s,\text{out}}}{P_{s,\text{in}}} \le 1 + \frac{\lambda_p P_{p,\text{in}}}{\lambda_s P_{s,\text{in}}}$$

we also see that in order to achieve a specific maximum gain G, the input signal power cannot exceed a value given by

$$P_{s,\text{in}} \leq \frac{(\lambda_p/\lambda_s)P_{p,\text{in}}}{G-1}$$

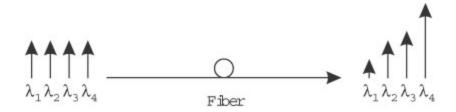
Raman Amplifiers

- Power transferred from lower-1 to higher-1 channels (about 100nm)
- Eg: 1460-1480nm pump \rightarrow amplification at 1550-1600nm
- Gain can be provided at ANY wavelength (all you need is an appropriate pump 1!)
- Multiple pumps can be used

Lumped or distributed designs possible

• Used today to complement EDFAs in ultra-long-haul systems

Raman Amplifier



Raman Amplifier

